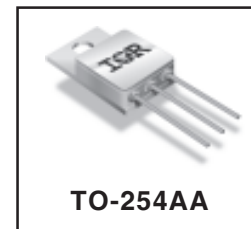


**RADIATION HARDENED  
POWER MOSFET  
THRU-HOLE (TO-254AA)**

**IRHM7460SE  
JANSR2N7392  
500V, N-CHANNEL  
REF: MIL-PRF-19500/661  
RAD Hard™ HEXFET® TECHNOLOGY**

**Product Summary**

Part Number	Radiation Level	R <sub>DS(on)</sub>	I <sub>D</sub>	QPL Part Number
IRHM7460SE	100K Rads (Si)	0.32Ω	18A	JANSR2N7392



International Rectifier's RADHard™ HEXFET® MOSFET technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low R<sub>DS(on)</sub> and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

**Features:**

- Single Event Effect (SEE) Hardened
- Ultra Low R<sub>DS(on)</sub>
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Light Weight
- ESD Rating: Class 3B per MIL-STD-750, Method 1020

**Absolute Maximum Ratings**

**Pre-Irradiation**

	Parameter		Units
I <sub>D</sub> @ V <sub>GS</sub> = 12V, T <sub>C</sub> = 25°C	Continuous Drain Current	18	A
I <sub>D</sub> @ V <sub>GS</sub> = 12V, T <sub>C</sub> = 100°C	Continuous Drain Current	11.7	
I <sub>DM</sub>	Pulsed Drain Current ①	72	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Max. Power Dissipation	250	W
	Linear Derating Factor	2.0	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	500	mJ
I <sub>AR</sub>	Avalanche Current ①	18	A
EAR	Repetitive Avalanche Energy ①	25	mJ
dv/dt	Peak Diode Recovery dv/dt ③	3.8	V/ns
T <sub>J</sub>	Operating Junction	-55 to 150	°C
T <sub>STG</sub>	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10 sec.)	
	Weight	9.3 (Typical)	g

For footnotes refer to the last page

**Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)**

Parameter		Min	Typ	Max	Units	Test Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	500	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	—	0.66	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DSON</sub>	Static Drain-to-Source On-State Resistance	—	—	0.32	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> = 11.7A ④ V <sub>GS</sub> = 12V, I <sub>D</sub> = 18A
		—	—	0.36		
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.5	—	4.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.0mA
g <sub>fs</sub>	Forward Transconductance	6.0	—	—	S	V <sub>DS</sub> = 15V, I <sub>DS</sub> = 11.7A ④
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	—	50	μA	V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
		—	—	250		
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	180	nC	V <sub>GS</sub> = 12V, I <sub>D</sub> = 18A V <sub>DS</sub> = 250V
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	30		
Q <sub>gd</sub>	Gate-to-Drain ('Miller') Charge	—	—	95		
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	29	ns	V <sub>DD</sub> = 250V, I <sub>D</sub> = 18A, V <sub>GS</sub> = 12V, R <sub>G</sub> = 2.35Ω
t <sub>r</sub>	Rise Time	—	—	93		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	90		
t <sub>f</sub>	Fall Time	—	—	59		
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	6.8	—	nH	Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package)
C <sub>iss</sub>	Input Capacitance	—	3500	—	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	730	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	260	—		

**Source-Drain Diode Ratings and Characteristics**

Parameter		Min	Typ	Max	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	18	A	
I <sub>SM</sub>	Pulse Source Current (Body Diode) ①	—	—	72		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.8	V	T <sub>j</sub> = 25°C, I <sub>S</sub> = 18A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	—	800	ns	T <sub>j</sub> = 25°C, I <sub>F</sub> = 18A, di/dt ≤ 100A/μs
Q <sub>RR</sub>	Reverse Recovery Charge	—	—	16	μC	V <sub>DD</sub> ≤ 50V ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> .				

**Thermal Resistance**

Parameter		Min	Typ	Max	Units	Test Conditions
R <sub>thJC</sub>	Junction-to-Case	—	—	0.50	°C/W	Typical socket mount
R <sub>thCS</sub>	Case-to-Sink	—	0.21	—		
R <sub>thJA</sub>	Junction-to-Ambient	—	—	48		

Note: Corresponding Spice and Saber models are available on International Rectifier Website.

For footnotes refer to the last page

## Pre-Irradiation

## IRHM7460SE, JANSR2N7392

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

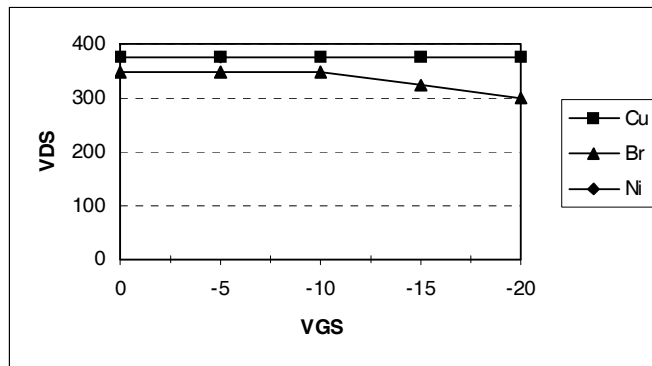
**Table 1. Electrical Characteristics @ T<sub>j</sub> = 25°C, Post Total Dose Irradiation ⑤⑥**

	Parameter	100K Rads (Si)		Units	Test Conditions
		Min	Max		
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	500	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	4.5		V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1.0mA
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	-100		V <sub>GS</sub> = -20V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	50	μA	V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V
R <sub>DS(on)</sub>	Static Drain-to-Source <sup>④</sup> On-State Resistance (TO-3)	—	0.32	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> = 11.7A
R <sub>DS(on)</sub>	Static Drain-to-Source <sup>④</sup> On-State Resistance (TO-254)	—	0.32	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> = 11.7A
V <sub>SD</sub>	Diode Forward Voltage <sup>④</sup>	—	1.8	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 18A

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

**Table 2. Typical Single Event Effect Safe Operating Area**

Ion	LET MeV/(mg/cm <sup>2</sup> )	Energy (MeV)	Range (μm)	V <sub>DS</sub> (V)				
				@V <sub>GS</sub> = 0V	@V <sub>GS</sub> = -5V	@V <sub>GS</sub> = -10V	@V <sub>GS</sub> = -15V	@V <sub>GS</sub> = -20V
Cu	28	285	43	375	375	375	375	375
Br	36.8	305	39	350	350	350	325	300
Ni	26.6	265	42	—	375	—	—	—



**Fig a. Typical Single Event Effect, Safe Operating Area**

For footnotes refer to the last page

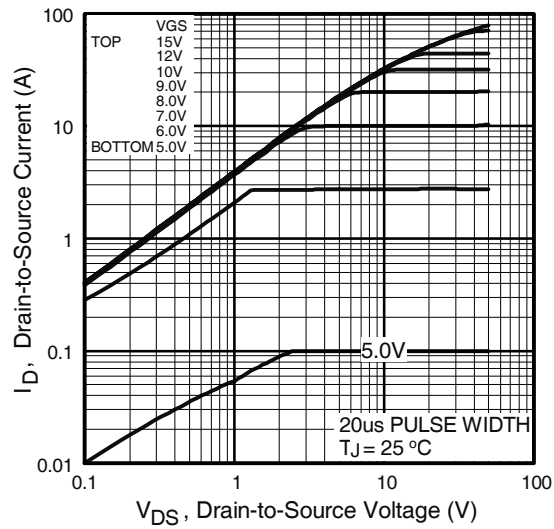


Fig 1. Typical Output Characteristics

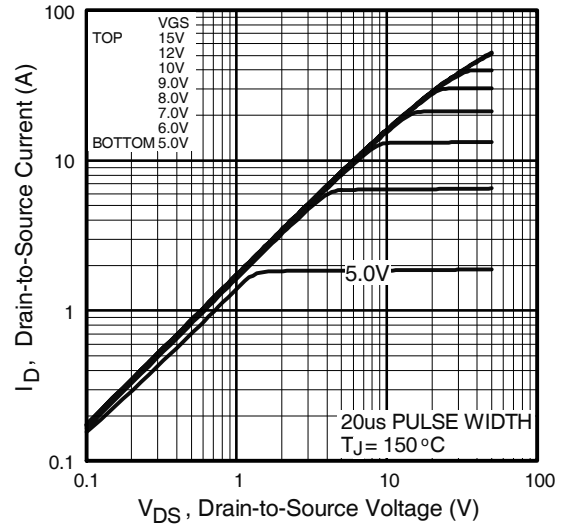


Fig 2. Typical Output Characteristics

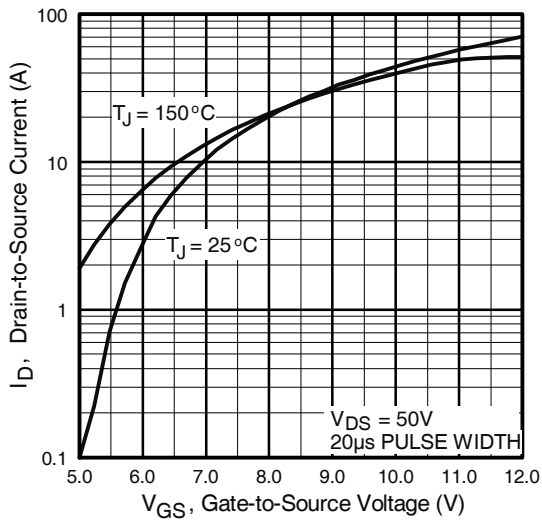


Fig 3. Typical Transfer Characteristics

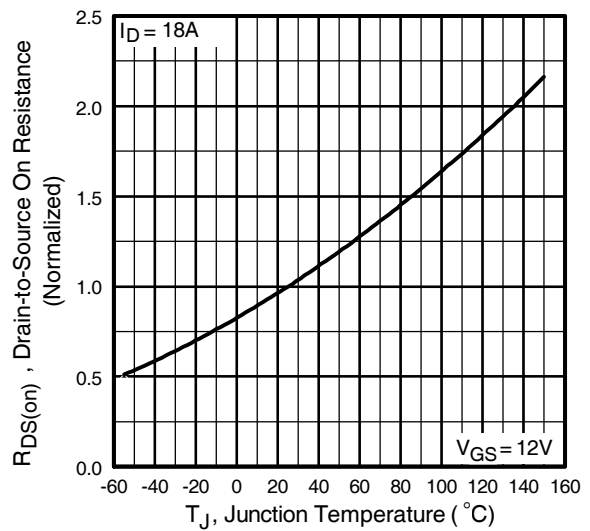


Fig 4. Normalized On-Resistance Vs. Temperature

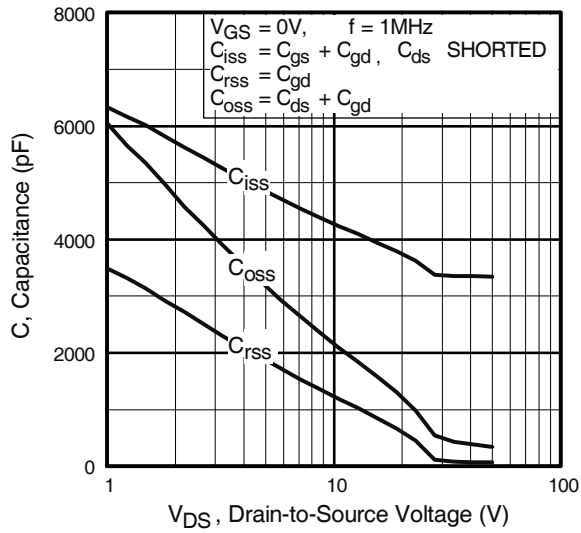


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

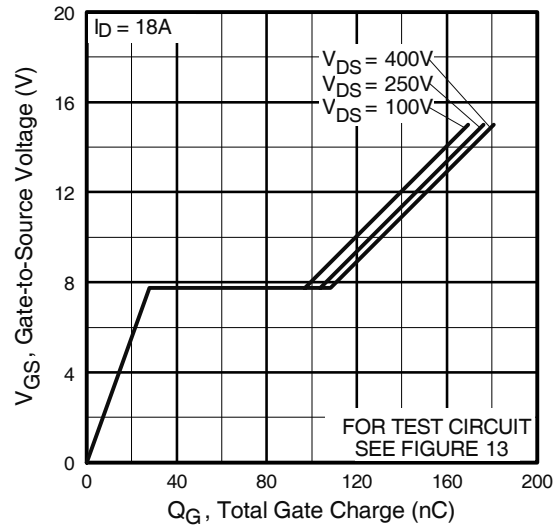


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

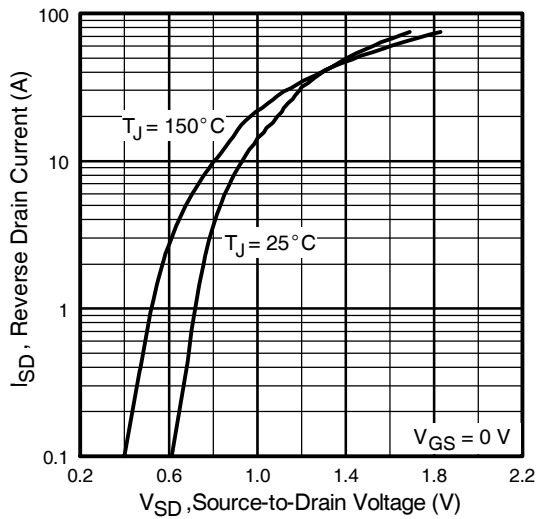


Fig 7. Typical Source-Drain Diode Forward Voltage

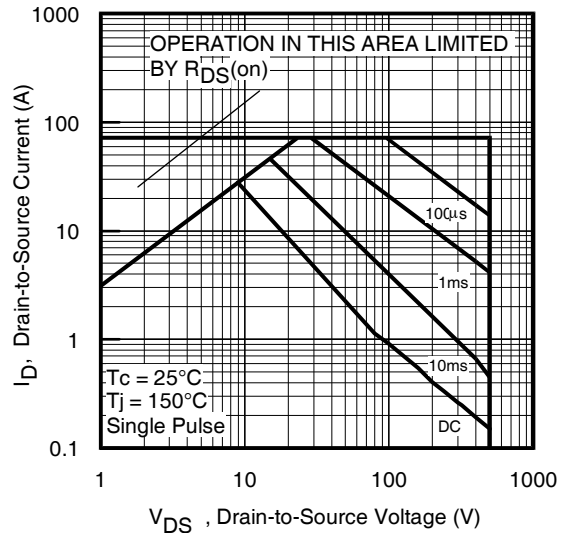


Fig 8. Maximum Safe Operating Area

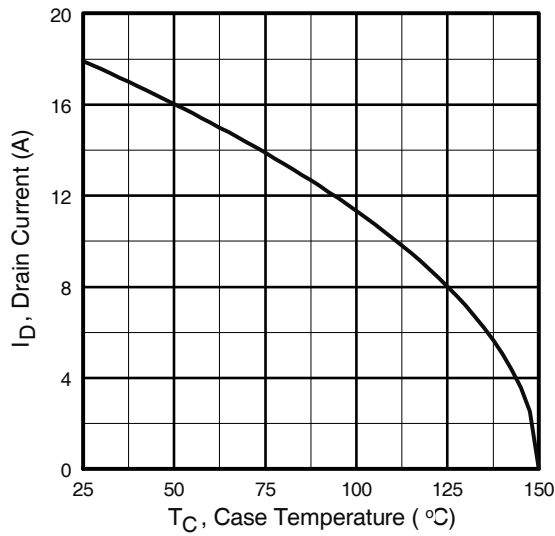


Fig 9. Maximum Drain Current Vs. Case Temperature

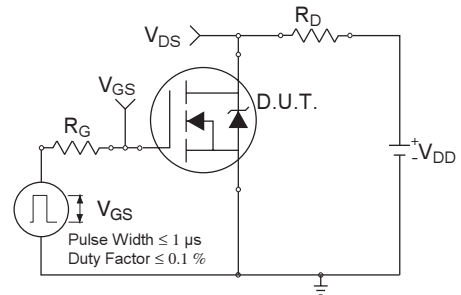


Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

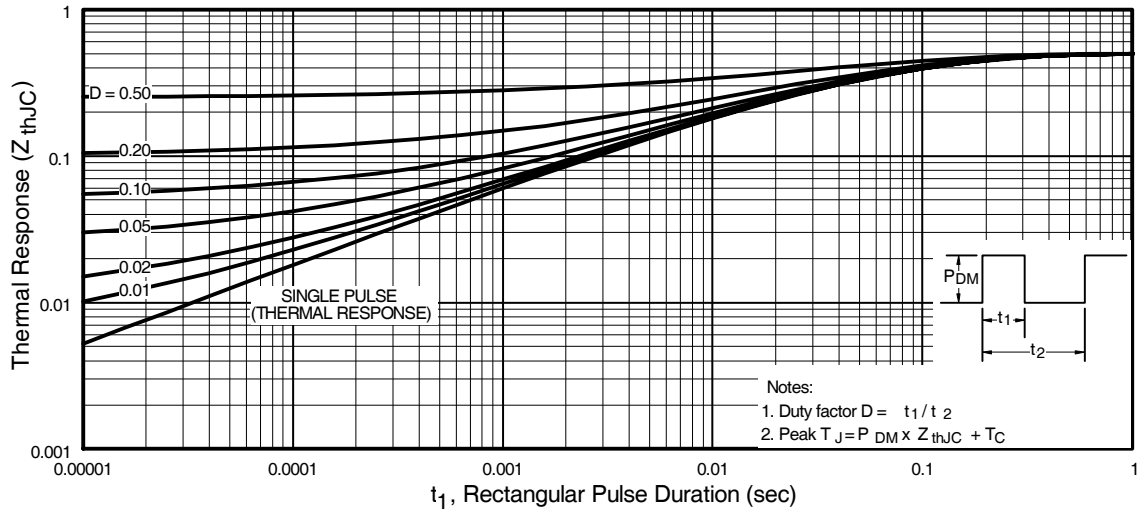


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

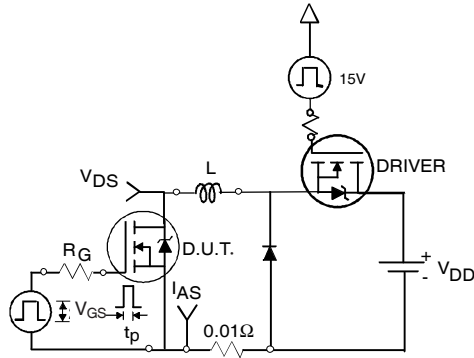


Fig 12a. Unclamped Inductive Test Circuit

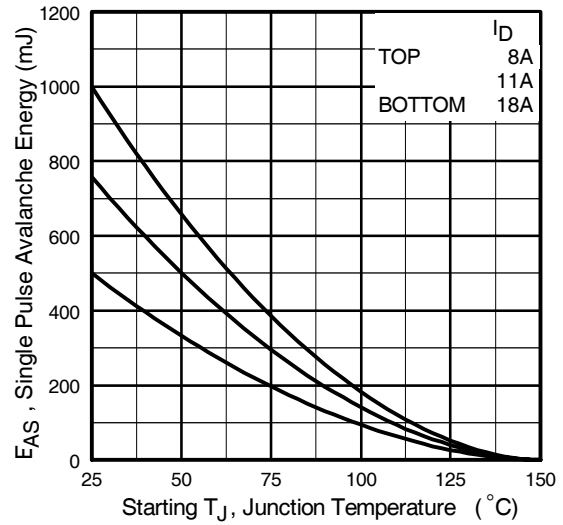


Fig 12c. Maximum Avalanche Energy Vs. Drain Current



Fig 12b. Unclamped Inductive Waveforms

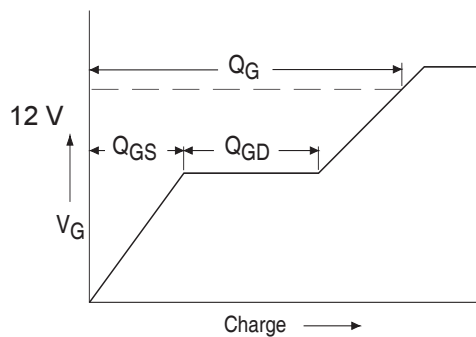


Fig 13a. Basic Gate Charge Waveform

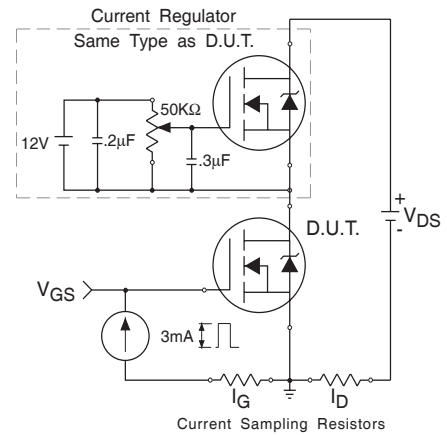
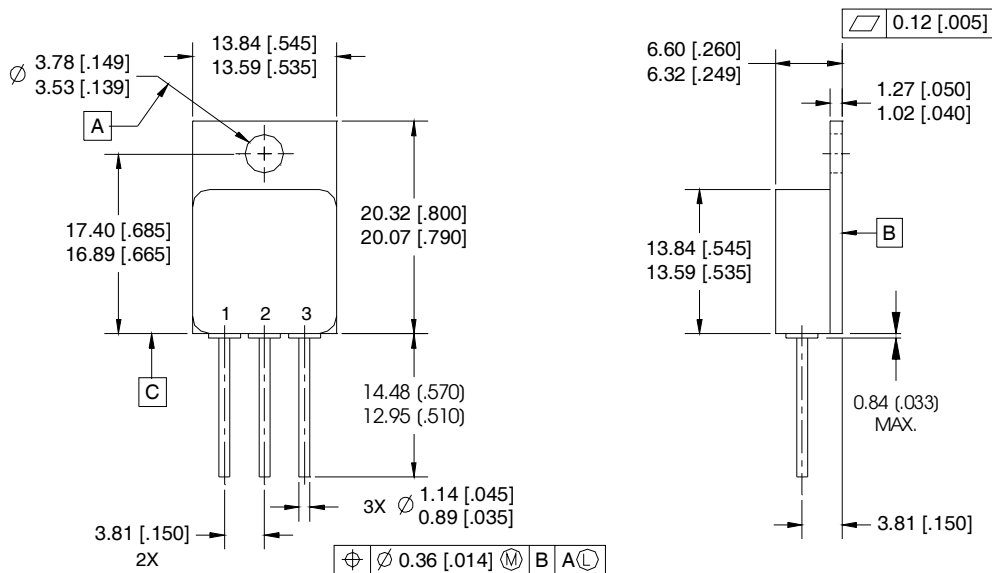


Fig 13b. Gate Charge Test Circuit

**Footnotes:**

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = 50V$ , starting  $T_J = 25^\circ C$ ,  $L = 3.1\text{ mH}$   
Peak  $I_L = 18A$ ,  $V_{GS} = 12V$
- ③  $I_{SD} \leq 18A$ ,  $di/dt \leq 110A/\mu s$ ,  
 $V_{DD} \leq 500V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300\ \mu s$ ; Duty Cycle  $\leq 2\%$
- ⑤ **Total Dose Irradiation with  $V_{GS}$  Bias.**  
12 volt  $V_{GS}$  applied and  $V_{DS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with  $V_{DS}$  Bias.**  
400 volt  $V_{DS}$  applied and  $V_{GS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.

**Case Outline and Dimensions —TO-254AA**



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: INCH.
4. CONFORMS TO JEDEC OUTLINE TO-254AA.

PIN ASSIGNMENTS

- 1 = DRAIN
- 2 = SOURCE
- 3 = GATE

**CAUTION**

**BERYLLIA WARNING PER MIL-PRF-19500**

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

International  
**IOR** Rectifier

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Visit us at [www.irf.com](http://www.irf.com) for sales contact information.

Data and specifications subject to change without notice. 06/2014



单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)